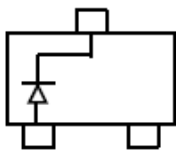
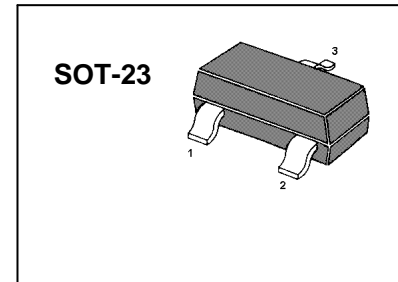
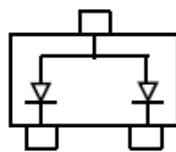
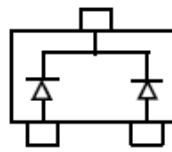
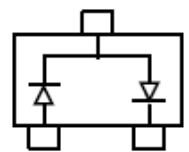


BAS21... SWITCHING DIODE

FEATURES

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- For General Purpose Switching Applications
- High Conductance


BAS21
Marking: JS

BAS21A
Marking: JS2

BAS21C
Marking: JS3

BAS21S
Marking: JS4

Maximum Ratings @ $T_A=25^{\circ}\text{C}$

Parameter	Symbol	Limits	Unit
Repetitive peak reverse voltage	V_{RRM}	250	V
Working Peak reverse voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Forward Continuous Current	I_{FM}	400	mA
Average Rectified Output Current	I_O	200	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	@ $t = 1.0\mu\text{s}$ 2.5	A
		@ $t = 1.0\text{s}$ 0.5	
Repetitive Peak Forward Surge Current	I_{FRM}	625	mA
Power Dissipation	P_D	225	mW
Thermal Resistance. Junction to Ambient Air	$R_{\theta JA}$	556	$^{\circ}\text{C}/\text{W}$
Junction temperature	T_J	150	$^{\circ}\text{C}$
Storage temperature range	T_{STG}	-65-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu\text{A}$	250		V
Reverse voltage leakage current	I_R	$V_R = 200\text{V}$		1	μA
Forward voltage	V_F	$I_F = 100\text{mA}$ $I_F = 200\text{mA}$		1000 1250	mV
Diode capacitance	C_D	$V_R = 0\text{V}$, $f = 1\text{MHz}$		5	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 30\text{mA}$, $I_{rr} = 0.1 \times I_R$, $R_L = 100\Omega$		50	nS

Typical Characteristics

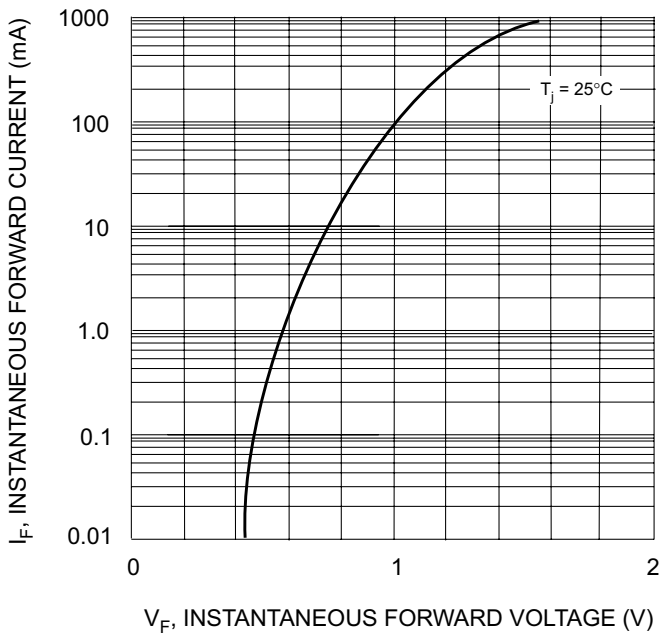


Fig. 1 Forward Characteristics

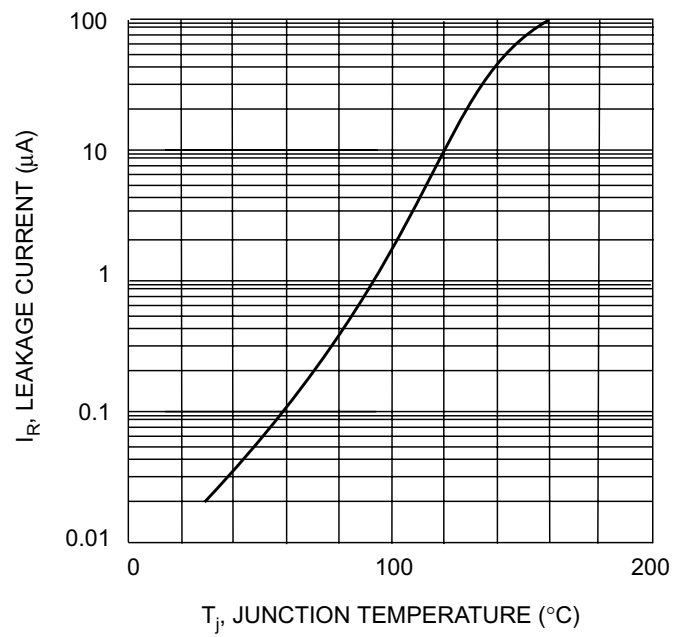
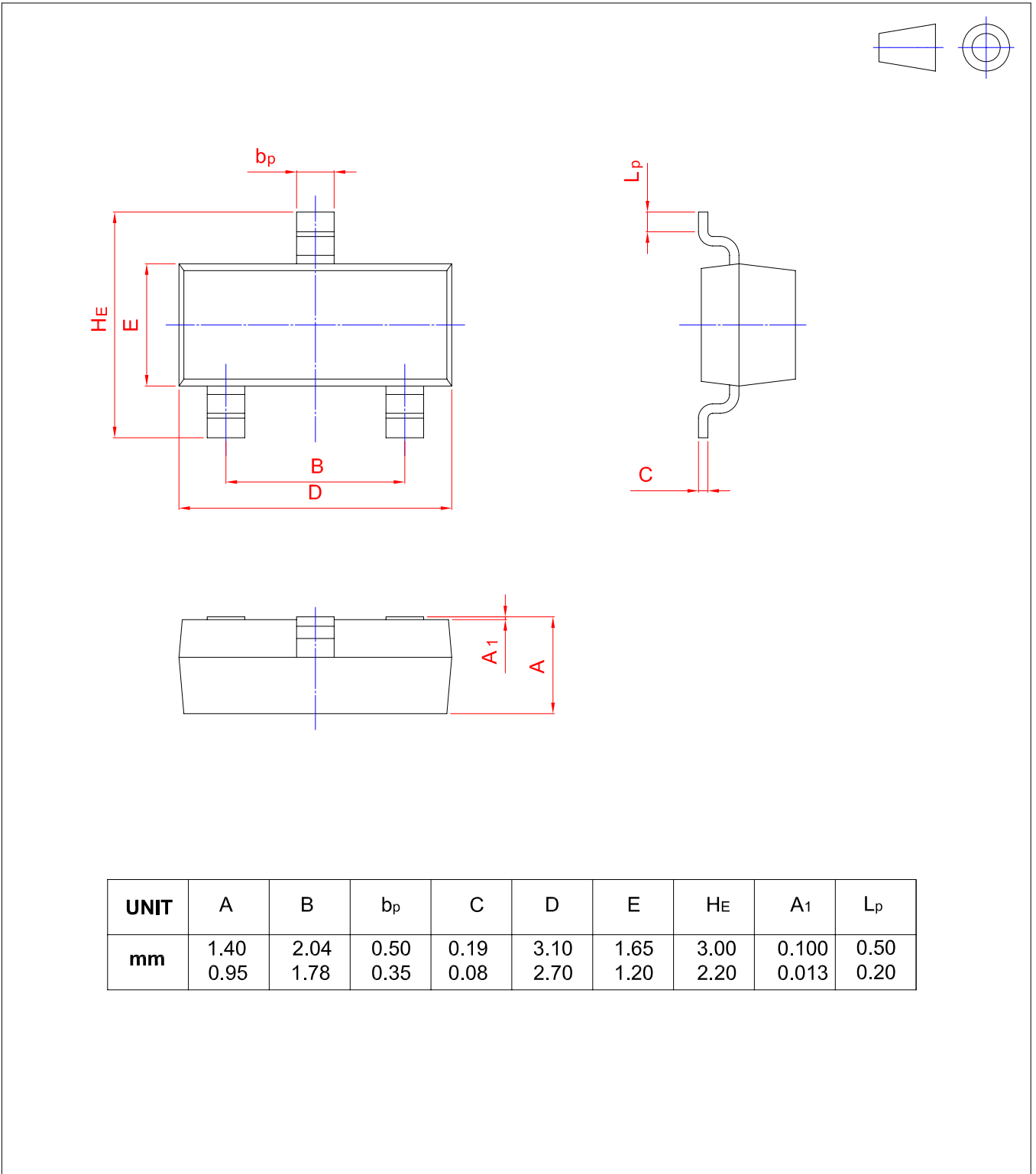


Fig. 2 Leakage Current vs Junction Temperature

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



单击下面可查看定价，库存，交付和生命周期等信息

[>>TWGMC\(台湾迪嘉\)](#)